

**P-Channel Enhancement Mode Power MOSFET**

**Description**

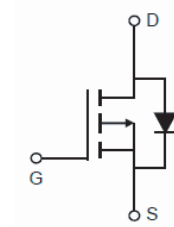
The RM60P04Y uses advanced trench technology and design to provide excellent  $R_{DS(ON)}$  with low gate charge .This device is well suited for use as a load switch or in PWM applications.

**General Features**

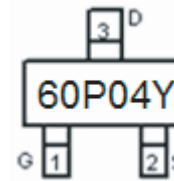
- $V_{DS} = -60V, I_D = -4A$   
 $R_{DS(ON)} < 120m\Omega @ V_{GS} = -10V$   
 $R_{DS(ON)} < 170m\Omega @ V_{GS} = -4.5V$
- High density cell design for ultra low  $R_{dson}$
- Fully characterized avalanche voltage and current
- Excellent package for good heat dissipation

**Application**

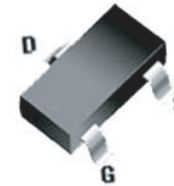
- Load switch
- PWM application



Schematic diagram



Marking and pin Assignment



SOT-23-3L top view

**Package Marking and Ordering Information**

Device Marking	Device	Device Package	Reel Size	Tape width	Quantity
60P04Y	RM60P04Y	SOT-23-3L	Ø180mm	8 mm	3000 units

**Absolute Maximum Ratings ( $T_c=25^\circ C$  unless otherwise noted)**

Parameter	Symbol	Limit	Unit
Drain-Source Voltage	$V_{DS}$	-60	V
Gate-Source Voltage	$V_{GS}$	$\pm 20$	V
Drain Current-Continuous	$I_D$	-4	A
Pulsed Drain Current	$I_{DM}$	-12	A
Maximum Power Dissipation	$P_D$	1.5	W
Operating Junction and Storage Temperature Range	$T_J, T_{STG}$	-55 To 150	$^\circ C$

**Thermal Characteristic**

Thermal Resistance, Junction-to-Ambient <sup>(Note 2)</sup>	$R_{\theta JA}$	83.3	$^\circ C/W$
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## Electrical Characteristics (T<sub>C</sub>=25°C unless otherwise noted)

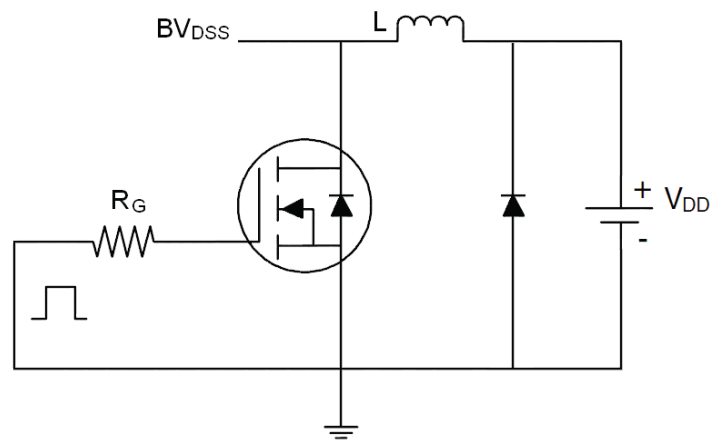
Parameter	Symbol	Condition	Min	Typ	Max	Unit
<b>Off Characteristics</b>						
Drain-Source Breakdown Voltage	BV <sub>DSS</sub>	V <sub>GS</sub> =0V, I <sub>D</sub> =-250μA	-60	-	-	V
Zero Gate Voltage Drain Current	I <sub>DSS</sub>	V <sub>DS</sub> =-60V, V <sub>GS</sub> =0V	-	-	-1	μA
Gate-Body Leakage Current	I <sub>GSS</sub>	V <sub>GS</sub> =±20V, V <sub>DS</sub> =0V	-	-	±100	nA
<b>On Characteristics</b> (Note 3)						
Gate Threshold Voltage	V <sub>GS(th)</sub>	V <sub>DS</sub> =V <sub>GS</sub> , I <sub>D</sub> =-250μA	-1.5	-2.2	-3.0	V
Drain-Source On-State Resistance	R <sub>DS(on)</sub>	V <sub>GS</sub> =-10V, I <sub>D</sub> =-4A	-	106	120	mΩ
		V <sub>GS</sub> =-4.5V, I <sub>D</sub> =-3A	-	135	170	mΩ
Forward Transconductance	g <sub>FS</sub>	V <sub>DS</sub> =-5V, I <sub>D</sub> =-4A	-	10	-	S
<b>Dynamic Characteristics</b> (Note 4)						
Input Capacitance	C <sub>iss</sub>	V <sub>DS</sub> =-30V, V <sub>GS</sub> =0V, F=1.0MHz	-	930	-	PF
Output Capacitance	C <sub>oss</sub>		-	85	-	PF
Reverse Transfer Capacitance	C <sub>rss</sub>		-	35	-	PF
<b>Switching Characteristics</b> (Note 4)						
Turn-on Delay Time	t <sub>d(on)</sub>	V <sub>DD</sub> =-30V, R <sub>L</sub> =7.5Ω, V <sub>GS</sub> =-10V, R <sub>G</sub> =3Ω	-	8	-	nS
Turn-on Rise Time	t <sub>r</sub>		-	4	-	nS
Turn-Off Delay Time	t <sub>d(off)</sub>		-	32	-	nS
Turn-Off Fall Time	t <sub>f</sub>		-	7	-	nS
Total Gate Charge	Q <sub>g</sub>	V <sub>DS</sub> =-30, I <sub>D</sub> =-4A, V <sub>GS</sub> =-10V	-	25	-	nC
Gate-Source Charge	Q <sub>gs</sub>		-	3	-	nC
Gate-Drain Charge	Q <sub>gd</sub>		-	7	-	nC
<b>Drain-Source Diode Characteristics</b>						
Diode Forward Voltage (Note 3)	V <sub>SD</sub>	V <sub>GS</sub> =0V, I <sub>S</sub> =-4A	-	-	-1.2	V
Diode Forward Current (Note 2)	I <sub>S</sub>		-	-	-4	A
Reverse Recovery Time	t <sub>rr</sub>	T <sub>J</sub> = 25°C, I <sub>F</sub> = -4A di/dt = -100A/μs (Note 3)	-	25		nS
Reverse Recovery Charge	Q <sub>rr</sub>		-	31		nC

### Notes:

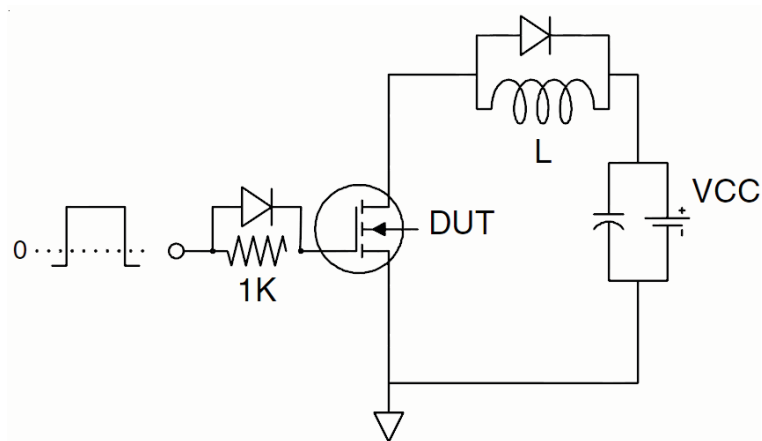
1. Repetitive Rating: Pulse width limited by maximum junction temperature.
2. Surface Mounted on FR4 Board, t ≤ 10 sec.
3. Pulse Test: Pulse Width ≤ 300μs, Duty Cycle ≤ 2%.
4. Guaranteed by design, not subject to production

## Test Circuit

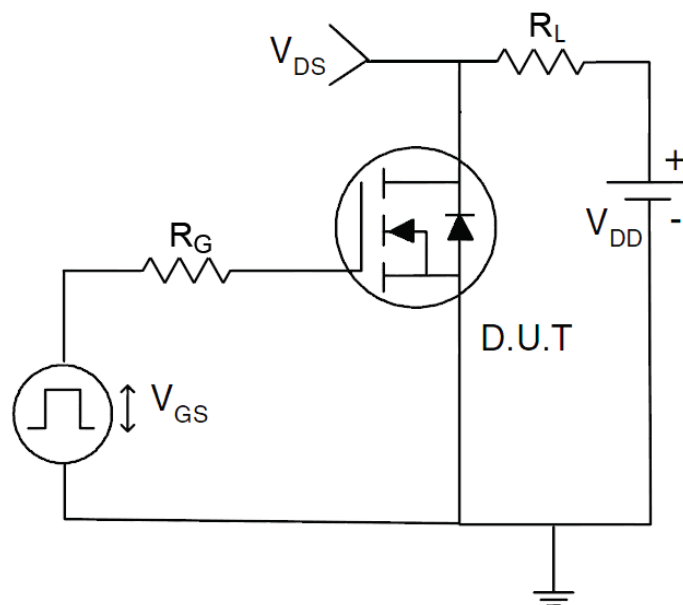
### 1) $E_{AS}$ test Circuit



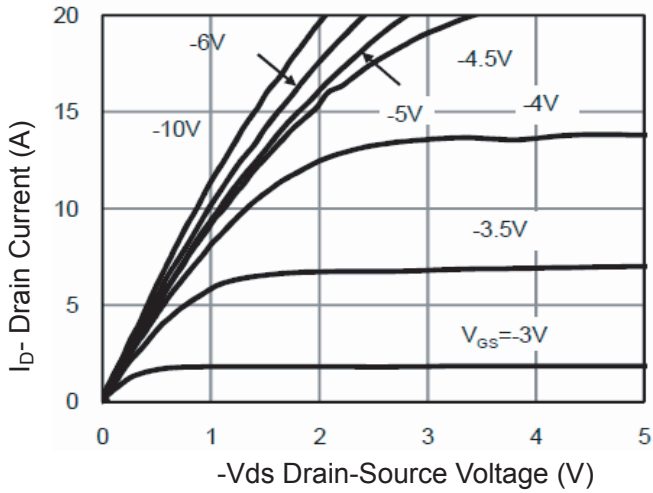
### 2) Gate charge test Circuit



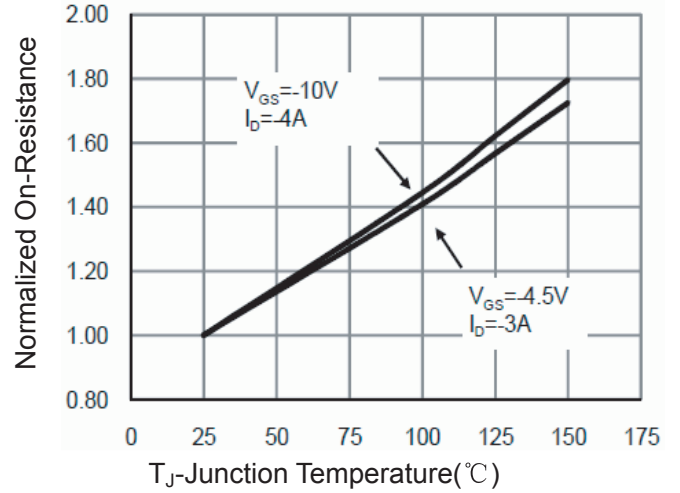
### 3) Switch Time Test Circuit



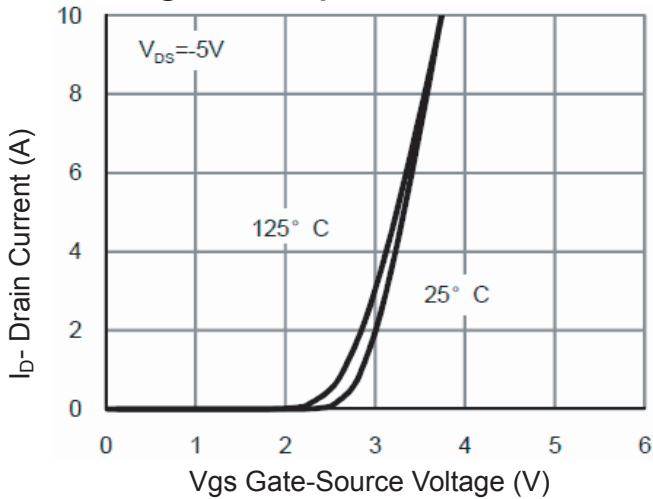
## RATING AND CHARACTERISTICS CURVES (RM60P04Y)



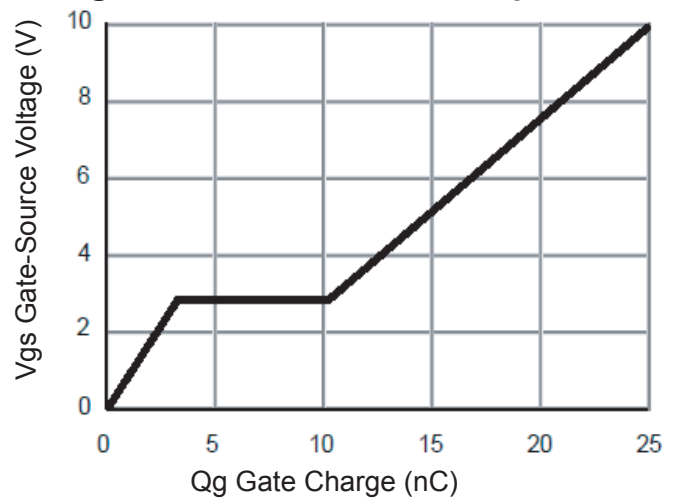
**Figure 1 Output Characteristics**



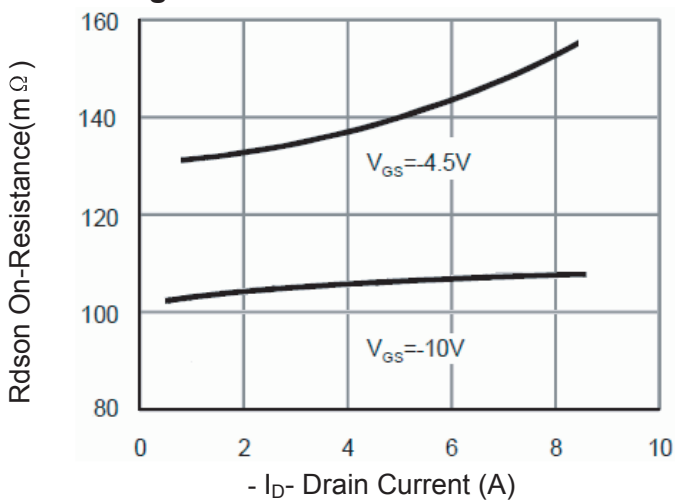
**Figure 4 Rdson-Junction Temperature**



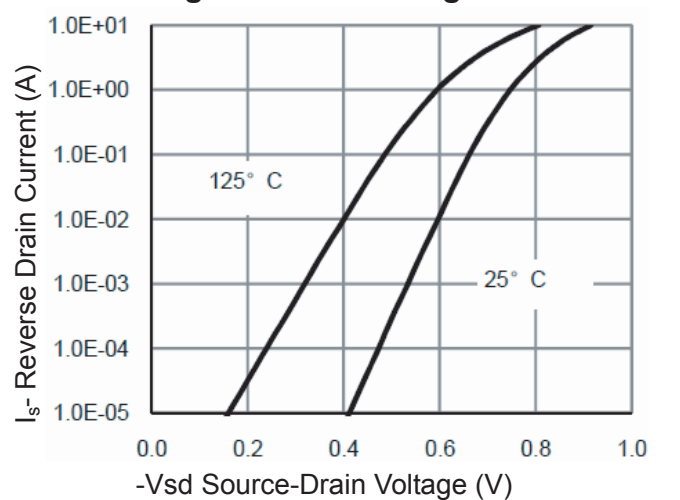
**Figure 2 Transfer Characteristics**



**Figure 5 Gate Charge**



**Figure 3 Rdson- Drain Current**



**Figure 6 Source- Drain Diode Forward**

## RATING AND CHARACTERISTICS CURVES (RM60P04Y)

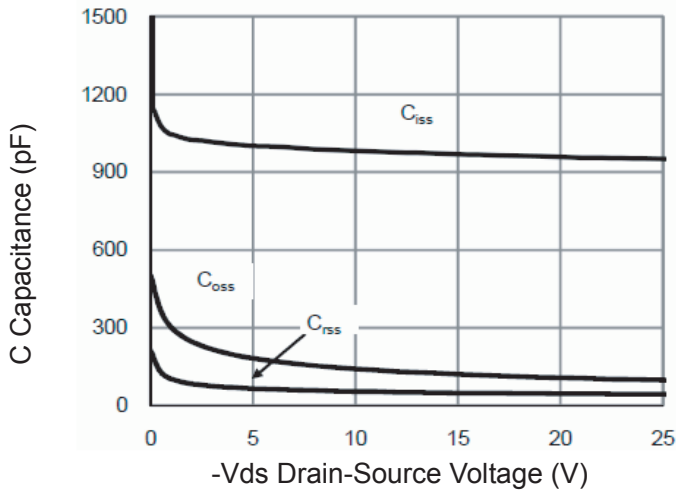


Figure 7 Capacitance vs Vds

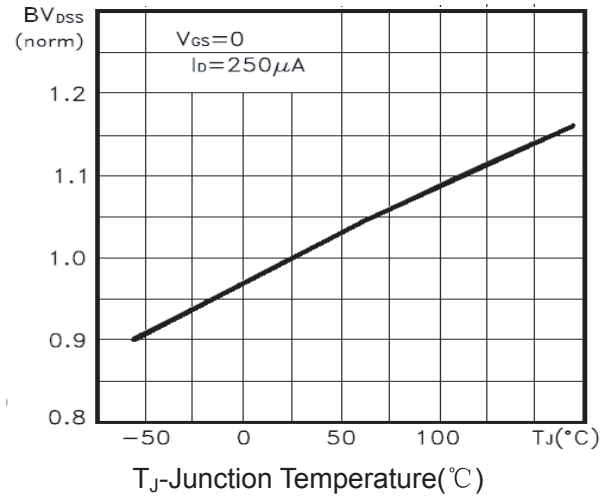


Figure 9  $BV_{DSS}$  vs Junction Temperature

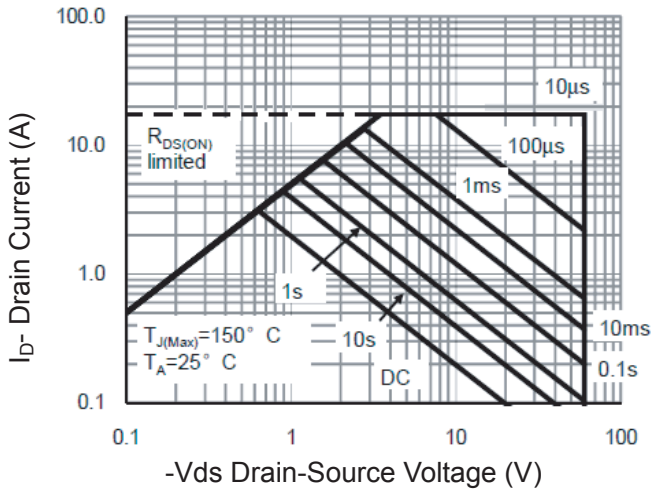


Figure 8 Safe Operation Area

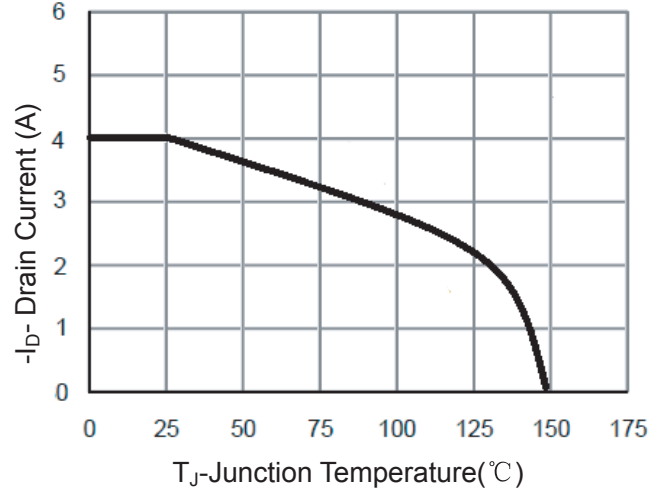


Figure 10  $I_D$  Current De-rating

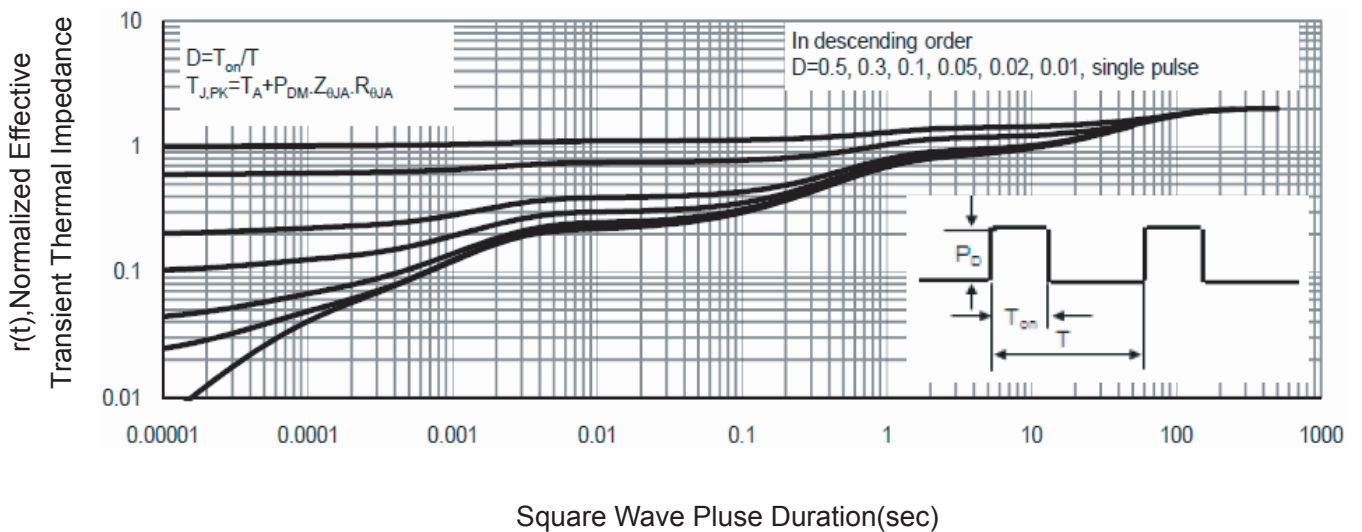
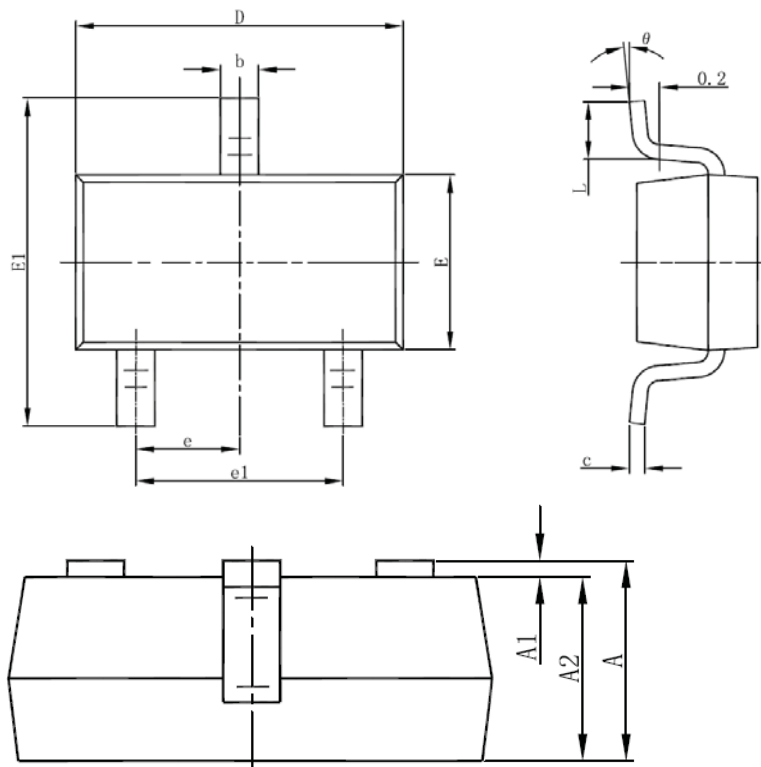


Figure 11 Normalized Maximum Transient Thermal Impedance

## SOT-23-3L Package Information



Symbol	Dimensions In Millimeters		Dimensions In Inches	
	Min	Max	Min	Max
A	1.050	1.250	0.041	0.049
A1	0.000	0.100	0.000	0.004
A2	1.050	1.150	0.041	0.045
b	0.300	0.500	0.012	0.020
c	0.100	0.200	0.004	0.008
D	2.820	3.020	0.111	0.119
E	1.500	1.700	0.059	0.067
E1	2.650	2.950	0.104	0.116
e	0.950(BSC)		0.037(BSC)	
e1	1.800	2.000	0.071	0.079
L	0.300	0.600	0.012	0.024
$\theta$	0°	8°	0°	8°

### Notes

1. All dimensions are in millimeters.
2. Tolerance  $\pm 0.10\text{mm}$  (4 mil) unless otherwise specified
3. Package body sizes exclude mold flash and gate burrs. Mold flash at the non-lead sides should be less than 5 mils.
4. Dimension L is measured in gauge plane.
5. Controlling dimension is millimeter, converted inch dimensions are not necessarily exact.